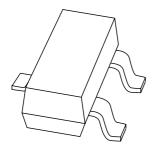
DISCRETE SEMICONDUCTORS

DATA SHEET



BF570NPN medium frequency transistor

Product data sheet Supersedes data of 2004 Jan 13 2004 Mar 15



NXP Semiconductors Product data sheet

NPN medium frequency transistor

BF570

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 15 V)
- Low feedback capacitance (max. 2.2 pF).

APPLICATIONS

- Monitors
- Battery equipped applications.

DESCRIPTION

NPN transistor in a SOT23 plastic package.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BF570	61* or B26

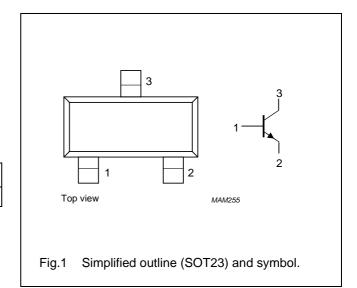
Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.

* = W : Made in China.

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



ORDERING INFORMATION

TYPE	PACKAGE		
NUMBER	NAME	ME DESCRIPTION VERSION	
BF570	_	plastic surface mounted package; 3 leads	

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V _{CEO}	collector-emitter voltage	open base	-	15	V
I _{CM}	peak collector current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	250	mW
h _{FE}	DC current gain	I _C = 10 mA; V _{CE} = 1 V	40	_	
f _T	transition frequency	I _C = 40 mA; V _{CE} = 10 V; f = 100 MHz	490	_	MHz

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NPN medium frequency transistor

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	40	V
V _{CEO}	collector-emitter voltage	open base	_	15	V
V _{EBO}	emitter-base voltage	open collector	_	4.5	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	500	K/W

CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0 A; V _{CB} = 20 V	_	_	400	nA
		I _E = 0 A; V _{CB} = 20 V; T _j = 125 °C	_	_	30	μΑ
I _{EBO}	emitter cut-off current	I _C = 0 A; V _{EB} = 2 V	_	_	100	nA
h _{FE}	DC current gain	I _C = 10 mA; V _{CE} = 1 V	40	_	_	
C _{re}	feedback capacitance	I _C = 0 A; V _{CE} = 10 V; f = 1 MHz	_	1.6	2.2	pF
f _T	transition frequency	I _C = 10 mA; V _{CE} = 10 V; f = 100 MHz	500	_	_	MHz
		I _C = 40 mA; V _{CE} = 10 V; f = 100 MHz	490	_	_	MHz

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NPN medium frequency transistor

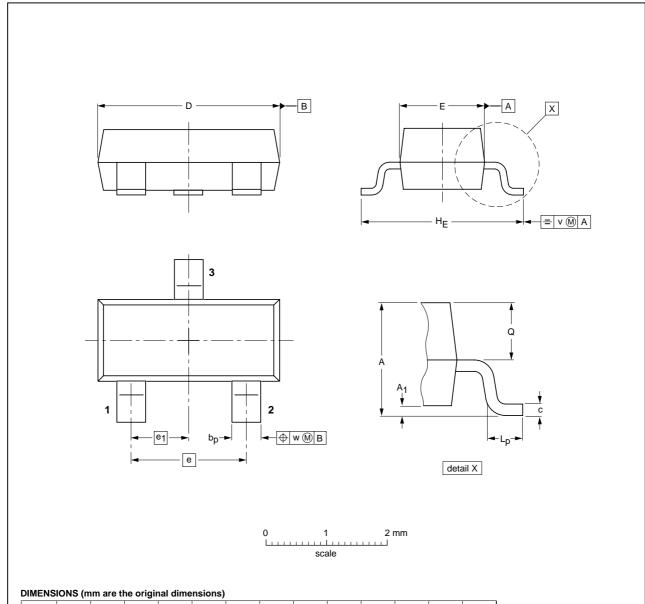
BF570

PACKAGE OUTLINE

UNIT

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ICCUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-04-11-04- 06-03-16

 ${\sf H}_{\sf E}$

 $\mathbf{L}_{\mathbf{p}}$

0.45

0.55

0.1

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bp

0.38

max

0.9

NXP Semiconductors Product data sheet

NPN medium frequency transistor

BF570

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published
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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

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